Triacs

## GENERAL DESCRIPTION

Glass passivated, sensitive gate triacs in a plastic envelope, intended for use in general purpose bidirectional switching and phase control applications. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

PINNING - SOT82

| PIN | DESCRIPTION |
| :---: | :--- |
| 1 | main terminal 1 |
| 2 | main terminal 2 |
| 3 | gate |
| tab | main terminal 2 |

## QUICK REFERENCE DATA

| SYMBOL | PARAMETER | MAX. | MAX. | UNIT |
| :---: | :---: | :---: | :---: | :---: |
| $\begin{aligned} & \mathrm{V}_{\text {DRM }} \\ & \mathrm{I}_{\mathrm{T}(\mathrm{RMS})} \\ & \mathrm{I}_{\text {TSM }} \end{aligned}$ | BT134- <br> Repetitive peak off-state voltages RMS on-state current Non-repetitive peak on-state current | $\begin{gathered} 500 \mathrm{D} \\ 500 \\ 4 \\ 25 \end{gathered}$ | $\begin{gathered} \text { 600D } \\ 600 \\ 4 \\ 25 \end{gathered}$ | $\begin{aligned} & \text { V } \\ & \text { A } \\ & \text { A } \end{aligned}$ |

## PIN CONFIGURATION



SYMBOL


## LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. |  | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $V_{\text {DRM }}$ | Repetitive peak off-state voltages |  |  | $\begin{aligned} & \hline-500 \\ & 500^{1} \end{aligned}$ | $\begin{aligned} & \hline-600 \\ & 600^{1} \end{aligned}$ | V |
| $\begin{aligned} & \mathrm{I}_{\text {T(RMS) }} \\ & \mathrm{T}_{\text {TSM }} \end{aligned}$ | RMS on-state current Non-repetitive peak on-state current | full sine wave; $\mathrm{T}_{\mathrm{mb}} \leq 107^{\circ} \mathrm{C}$ full sine wave; $\mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$ prior to surge$\begin{aligned} & \mathrm{t}=20 \mathrm{~ms} \\ & \mathrm{t}=16.7 \mathrm{~ms} \\ & \mathrm{t}=10 \mathrm{~ms} \\ & \mathrm{~T}_{1 \mathrm{M}}=6 \mathrm{~A} ; \mathrm{I}_{\mathrm{G}}=0.2 \mathrm{~A} ; \\ & \mathrm{d} \mathrm{I}_{\mathrm{G}} / \mathrm{dt}=0.2 \mathrm{~A} / \mu \mathrm{s} \end{aligned}$ |  | 4 |  | A |
|  |  |  |  | 27 |  | A |
| $\begin{aligned} & \mathrm{I}^{2} \mathrm{t} \\ & \mathrm{dl}_{\mathrm{T}} / \mathrm{dt} \end{aligned}$ | $I^{2}$ f for fusing Repetitive rate of rise of on-state current after |  | - |  |  | $A^{2} \mathrm{~S}$ |
|  | triggering |  |  |  | $50$ | A/ $/ \mathrm{s}$ A/ S |
|  |  |  | - | 50 |  | A/us |
|  | Peak gate current |  | - | 10 |  | A/ ${ }_{\text {A }}$ |
| $\mathrm{V}_{\mathrm{GM}}$ | Peak gate voltage |  | - | 5 |  | V |
|  | Peak gate power |  |  | 50.5 |  | W |
| $\mathrm{P}_{\mathrm{T}}^{\mathrm{G}(\mathrm{AV})}$ | Average gate power |  | -40 |  |  | W |
| $\mathrm{T}_{\mathrm{t} \text { stg }}$ | Storage temperature |  | -40 | 150 |  | ${ }^{\circ} \mathrm{C}$ |
| $\mathrm{T}_{\mathrm{j}}$ | Operating junction temperature |  |  | 125 |  | ${ }^{\circ} \mathrm{C}$ |

[^0]THERMAL RESISTANCES

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
| :--- | :--- | :--- | :---: | :---: | :---: | :---: |
| $\mathrm{R}_{\mathrm{th} j-\mathrm{mb}}$ | Thermal resistance <br> junction to mounting base | full cycle <br> half cycle <br> $\mathrm{R}_{\mathrm{th} j-\mathrm{a}}$ | Thermal resistance <br> junction to ambient | in free air | - | - |
| 3.0 | $\mathrm{~K} / \mathrm{W}$ |  |  |  |  |  |

## STATIC CHARACTERISTICS

$\mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$ unless otherwise stated

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{I}_{\mathrm{GT}}$ | Gate trigger current | $\mathrm{V}_{\mathrm{D}}=12 \mathrm{~V} ; \mathrm{I}_{\mathrm{T}}=0.1 \mathrm{~A}$ |  |  |  |  |
|  |  | T2+ G+ T2+ G- |  | 2.0 2.5 |  | mA |
|  |  | T2- G- |  | 2.5 | 5 | mA |
|  |  | $V_{D}=12 \mathrm{~V} \cdot \mathrm{I}_{\mathrm{T}}=0.1 \mathrm{~A} \quad$ T2-G+ |  | 5.0 | 10 | mA |
| $L_{L}$ | Latching current | $\mathrm{V}_{\mathrm{D}}=12 \mathrm{~V}, \mathrm{l}_{\mathrm{GT}}=0.1 \mathrm{~A} \quad \mathrm{~T} 2+\mathrm{G}+$ |  | 1.6 | 10 | mA |
|  |  | T2+ G- |  | 4.5 | 15 | mA |
|  |  | T2- G- |  | 1.2 | 10 | mA |
|  |  |  |  | 2.2 | 15 | mA |
|  | Holding current | $\mathrm{V}_{\mathrm{D}}=12 \mathrm{~V} ; \mathrm{I}_{\mathrm{GT}}=0.1 \mathrm{~A}$ |  | 1.2 | 10 | mA |
|  | On-state voltage | $\mathrm{I}_{\mathrm{T}}=5 \mathrm{~A}$ |  | 1.4 | 1.70 | V |
| $V_{G T}$ | Gate trigger voltage | V ${ }^{\text {V }}$ |  | 0.7 | 1.5 | V |
| $\mathrm{I}_{\mathrm{D}}$ | Off-state leakage current | $\mathrm{V}_{\text {D }}=400 \mathrm{~V} ; \mathrm{I}_{T}=0.1 \mathrm{~A} ; \mathrm{T}_{\mathrm{j}}=125^{\circ} \mathrm{C}$ $\mathrm{V}_{\mathrm{D}}=\mathrm{V}_{\text {DRM (max }} ; \mathrm{T}_{\mathrm{j}}=125{ }^{\circ} \mathrm{C}$ | 0.25 | 0.4 0.1 | - 0 | $\stackrel{\mathrm{V}}{\mathrm{mA}}$ |

## DYNAMIC CHARACTERISTICS

$\mathrm{T}_{\mathrm{j}}=25^{\circ} \mathrm{C}$ unless otherwise stated

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
| :---: | :---: | :---: | :---: | :---: | :---: | :---: |
| $\mathrm{dV}_{\mathrm{D}} / \mathrm{dt}$ | Critical rate of rise of | $\mathrm{V}_{\text {DM }}=67 \% \mathrm{~V}_{\text {DRM(max }} ; \mathrm{T}_{j}=125^{\circ} \mathrm{C} ;$ |  | 5 | - | V/us |
|  | off-state voltage Gate controlled turn-on | exponential waveform; $\mathrm{R}_{\mathrm{GK}}=1 \mathrm{k} \Omega$ |  | 2 |  |  |
| $\mathrm{tgt}_{\mathrm{gt}}$ | Gate controlied turn-on time | $\mathrm{I}_{\mathrm{TM}}=6 \mathrm{~A} ; \mathrm{V}_{\mathrm{D}}=\mathrm{V}_{\mathrm{DRM}(\max )} ; \mathrm{I}_{\mathrm{G}}=0.1 \mathrm{~A}$; $\mathrm{dl}_{\mathrm{G}} / \mathrm{dt}=5 \mathrm{~A} / \mu \mathrm{s}$ | - | 2 | - | $\mu \mathrm{S}$ |



Fig.1. Maximum on-state dissipation, $P_{\text {tot }}$, versus rms on-state current, $I_{T(\text { RMS })}$, where $\alpha=$ conduction angle.


Fig.2. Maximum permissible non-repetitive peak on-state current $I_{\text {TSM }}$, versus pulse width $t_{p}$, for sinusoidal currents, $t_{p} \leq 20 \mathrm{~ms}$.


Fig.3. Maximum permissible non-repetitive peak on-state current $l_{\text {TSM }}$, versus number of cycles, for sinusoidal currents, $f=50 \mathrm{~Hz}$.


Fig.4. Maximum permissible rms current $I_{T(R M S)}$, versus mounting base temperature $T_{m b}$.


Fig.5. Maximum permissible repetitive rms on-state current $I_{T(R M S)}$, versus surge duration, for sinusoidal currents, $f=50 \mathrm{~Hz} ; T_{m b} \leq 107^{\circ} \mathrm{C}$.


Fig.6. Normalised gate trigger voltage $V_{G T}\left(T_{j}\right) / V_{G T}\left(25^{\circ} \mathrm{C}\right)$, versus junction temperature $T_{j}$.


Fig.7. Normalised gate trigger current $I_{G T}\left(T_{j}\right) / I_{G T}\left(25^{\circ} \mathrm{C}\right)$, versus junction temperature $T_{j}$.


Fig.8. Normalised latching current $I_{L}\left(T_{T}\right) / I_{L}\left(25^{\circ} \mathrm{C}\right)$, versus junction temperature $T_{\text {. }}$.


Fig.9. Normalised holding current $I_{H}\left(T_{\mathcal{P}}\right) / I_{H}\left(25^{\circ} \mathrm{C}\right)$, versus junction temperature $T_{j}$.


Fig.10. Typical and maximum on-state characteristic.


Fig.11. Transient thermal impedance $Z_{\text {th } i \text {-mb }}$, versus pulse width $t_{p}$.


Fig.12. Typical, critical rate of rise of off-state voltage, $d V_{D} / d t$ versus junction temperature $T_{j}$.

## Triacs

## MECHANICAL DATA



Fig.13. SOT82; pin 2 connected to mounting base.

## Notes

1. Refer to mounting instructions for SOT82 envelopes.
2. Epoxy meets UL94 V0 at 1/8".

Triacs

## DEFINITIONS

| Data sheet status |  |
| :--- | :--- |
| Objective specification | This data sheet contains target or goal specifications for product development. |
| Preliminary specification | This data sheet contains preliminary data; supplementary data may be published later. |
| Product specification | This data sheet contains final product specifications. |
| Limiting values |  |
| Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one <br> or more of the limiting values may cause permanent damage to the device. These are stress ratings only and <br> operation of the device at these or at any other conditions above those given in the Characteristics sections of <br> this specification is not implied. Exposure to limiting values for extended periods may affect device reliability. |  |
| Application information |  |
| Where application information is given, it is advisory and does not form part of the specification. |  |
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## LIFE SUPPORT APPLICATIONS

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[^0]:    1 Although not recommended, off-state voltages up to 800 V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed $3 \mathrm{~A} / \mu \mathrm{s}$.

